

DESCRIPTION

The SSF2610E uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operate with gate voltages as low as 2.5V.

FEATURES

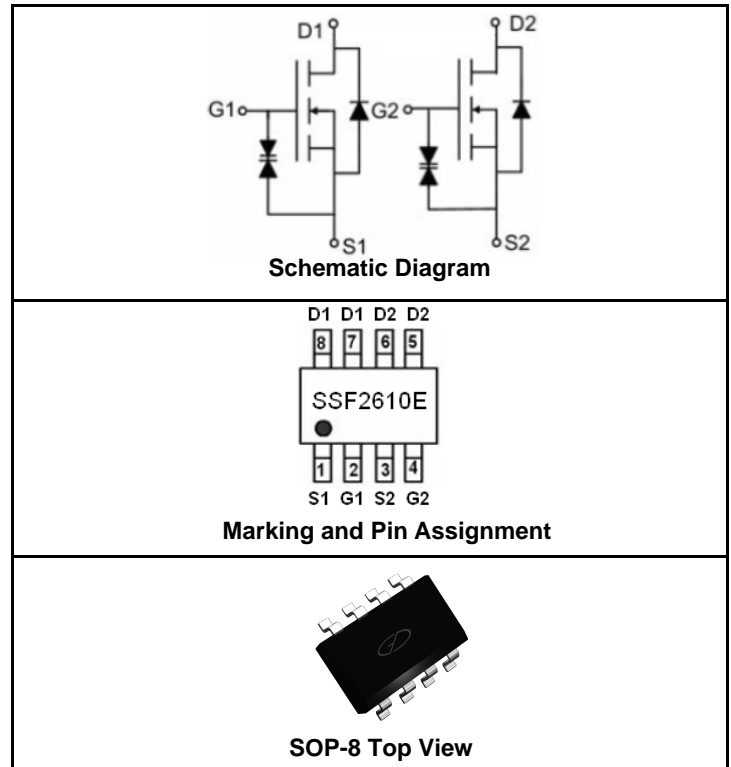
- $V_{DS} = 20V$, $I_D = 8A$
 $R_{DS(ON)} < 23m\Omega$ @ $V_{GS}=1.8V$
 $R_{DS(ON)} < 18m\Omega$ @ $V_{GS}=2.5V$
 $R_{DS(ON)} < 14m\Omega$ @ $V_{GS}=4.5V$

ESD Rating: 2000V HBM

- High Power and Current Handling Capability
- Lead Free
- Surface Mount Package

APPLICATIONS

- Battery Protection
- Load Switch
- Power Management



PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape Width	Quantity
SSF2610E	SSF2610E	SOP-8	Ø330mm	12mm	3000 units

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	$I_D(25^\circ C)$	8	A
	$I_D(70^\circ C)$	6.2	A
	I_{DM}	25	A
Maximum Power Dissipation	P_D	2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	83	$^\circ C/W$
--	-----------------	----	--------------

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 4.5V, V_{DS}=0V$			± 100	nA
		$V_{GS}=\pm 10V, V_{DS}=0V$			± 10	μA
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.6	0.75	1	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=8A$		11	14	m Ω
		$V_{GS}=2.5V, I_D=6.5A$		14	18	m Ω
		$V_{GS}=1.8V, I_D=6A$		20	23	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=6.5A$	5			S
DYNAMIC CHARACTERISTICS (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=8V, V_{GS}=0V,$ $F=1.0MHz$		600		PF
Output Capacitance	C_{oss}			330		PF
Reverse Transfer Capacitance	C_{rss}			140		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=1A$ $V_{GS}=4.5V, R_{GEN}=6\Omega$		10	20	nS
Turn-on Rise Time	t_r			11	25	nS
Turn-Off Delay Time	$t_{d(off)}$			35	70	nS
Turn-Off Fall Time	t_f			30	60	nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=8A,$ $V_{GS}=4.5V$		10	15	nC
Gate-Source Charge	Q_{gs}			2.3		nC
Gate-Drain Charge	Q_{gd}			3		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=1.5A$		0.84	1.2	V

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on 1in² FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

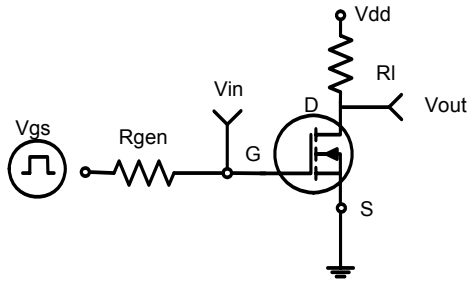


Figure 1. Switching Test Circuit

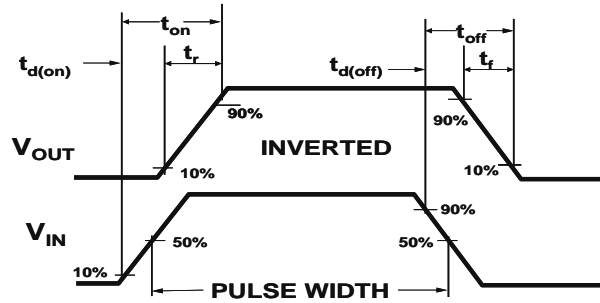


Figure 2. Switching Waveforms

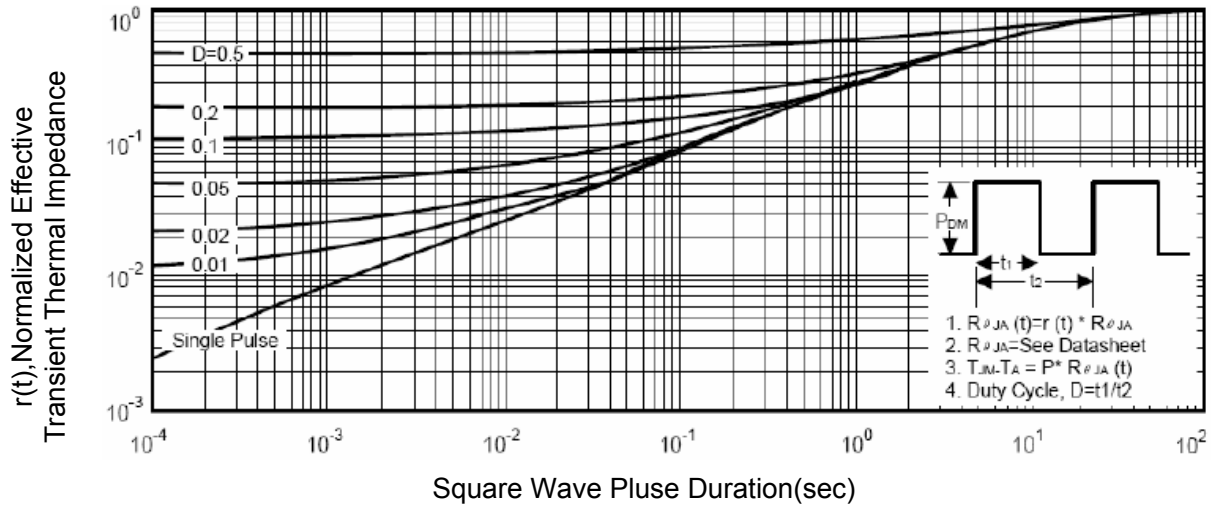
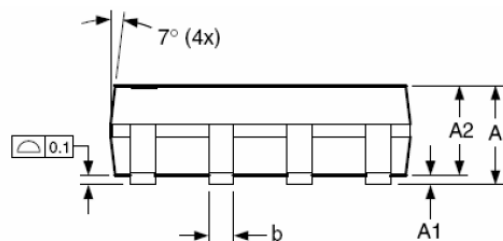
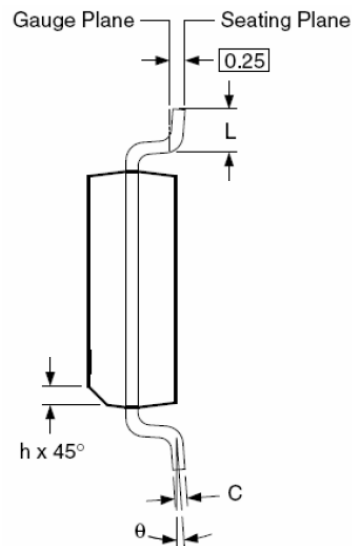
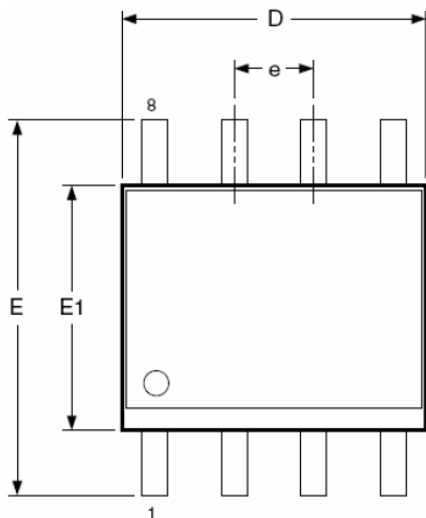
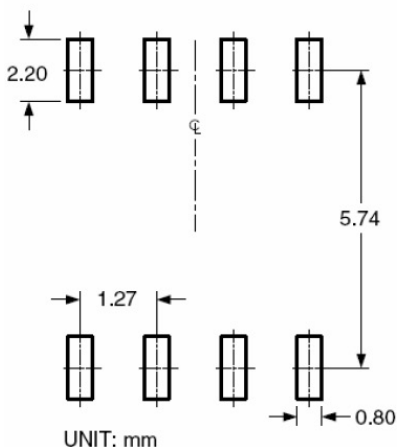


Figure 3. Normalized Maximum Transient Thermal Impedance

SOP-8 PACKAGE INFORMATION



RECOMMENDED LAND PATTERN



Dimensions in millimeters

Symbols	Min.	Nom.	Max.
A	1.35	1.65	1.75
A1	0.10	—	0.25
A2	1.25	1.50	1.65
b	0.31	—	0.51
c	0.17	—	0.25
D	4.80	4.90	5.00
E1	3.80	3.90	4.00
e	1.27 BSC		
E	5.80	6.00	6.20
h	0.25	—	0.50
L	0.40	—	1.27
θ	0°	—	8°

Dimensions in inches

Symbols	Min.	Nom.	Max.
A	0.053	0.065	0.069
A1	0.004	—	0.010
A2	0.049	0.059	0.065
b	0.012	—	0.020
c	0.007	—	0.010
D	0.189	0.193	0.197
E1	0.150	0.154	0.157
e	0.050 BSC		
E	0.228	0.236	0.244
h	0.010	—	0.020
L	0.016	—	0.050
θ	0°	—	8°

NOTES:

1. Dimensions are inclusive of plating
2. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 6 mils.
3. Dimension L is measured in gauge plane.
4. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.